

# MC100LVELT20

## 3.3 V LVTTTL/LVCMOS to Differential LVPECL Translator

### Description

The MC100LVELT20 is a 3.3 V TTL/CMOS to differential PECL translator. Because PECL (Positive ECL) levels are used, only + 3.3 V and ground are required. The small outline SOIC-8 package and the single gate of the MC100LVELT20 makes it ideal for those applications where space, performance, and low power are at a premium.

The 100 Series contains temperature compensation.

### Features

- 390 ps Typical Propagation Delay
- Maximum Input Clock Frequency > 0.8 GHz Typical
- Operating Range  $V_{CC} = 3.0\text{ V}$  to  $3.6\text{ V}$  with  $GND = 0\text{ V}$
- PNP TTL Input for Minimal Loading
- Q Output will Default HIGH with Input Open
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant



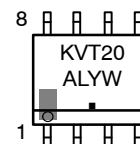
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SOIC-8 NB  
D SUFFIX  
CASE 751-07

### MARKING DIAGRAM



A = Assembly Location  
L = Wafer Lot  
Y = Year  
W = Work Week  
■ = Pb-Free Package

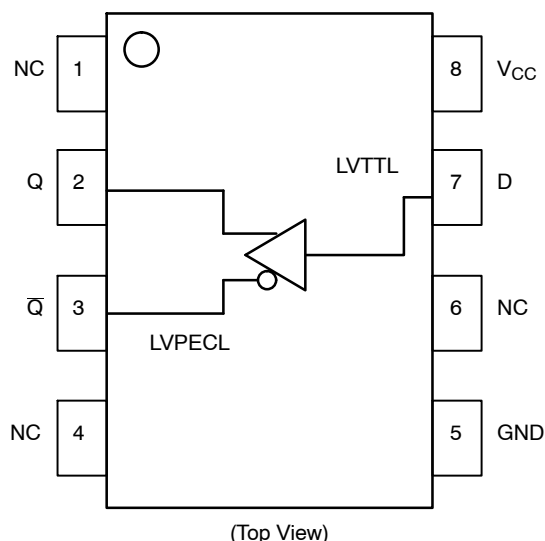
\*For additional marking information, refer to Application Note [AND8002/D](#).

### ORDERING INFORMATION

Device	Package	Shipping†
MC100LVELT20DG	SOIC-8 NB (Pb-Free)	98 Units/Tube
MC100LVELT20DR2G	SOIC-8 NB (Pb-Free)	2500/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

# MC100LVELT20



**Figure 1. 8-Lead Pinout and Logic Diagram**

**Table 1. PIN DESCRIPTION**

Pin	Function
Q, $\bar{Q}$	Differential PECL Outputs
D	LVTTTL Input
$V_{CC}$	Positive Supply
GND	Ground
NC	No Connect

**Table 2. ATTRIBUTES**

Characteristics	Value
Internal Input Pulldown Resistor	N/A
Internal Input Pullup Resistor	N/A
ESD Protection Human Body Model Machine Model Charged Device Model	> 1.5 kV > 200 V > 2 kV
Moisture Sensitivity, Indefinite Time Out of Drypack (Note 1)	Pb-Free Pkg
SOIC-8 NB	Level 1
Flammability Rating Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in
Transistor Count	150 Devices
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test	

1. For additional information, see Application Note [AND8003/D](#).

**Table 3. MAXIMUM RATINGS**

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
$V_{CC}$	Power Supply	GND = 0 V		6	V
$V_I$	Input Voltage	GND = 0 V	$V_I \leq V_{CC}$	6	V
$I_{out}$	Output Current	Continuous Surge		50 100	mA
$T_A$	Operating Temperature Range			-40 to +85	°C
$T_{stg}$	Storage Temperature Range			-65 to +150	°C
$\theta_{JA}$	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	SOIC-8 NB	190 130	°C/W
$\theta_{JC}$	Thermal Resistance (Junction-to-Case)	Standard Board	SOIC-8 NB	41 to 44	°C/W
$T_{sol}$	Wave Solder (Pb-Free)			265	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

# MC100LVELT20

**Table 4. LVTTTL INPUT DC CHARACTERISTICS** ( $V_{CC} = 3.3\text{ V}$ ,  $GND = 0\text{ V}$ ,  $T_A = -40^\circ\text{C}$  to  $+85^\circ\text{C}$ )

Symbol	Characteristic	Min	Typ	Max	Unit
$I_{IH}$	Input HIGH Current ( $V_{in} = 2.7\text{ V}$ )			20	$\mu\text{A}$
$I_{IHH}$	Input HIGH Current MAX ( $V_{in} = 6.0\text{ V}$ )			100	$\mu\text{A}$
$I_{IL}$	Input LOW Current ( $V_{in} = 0.5\text{ V}$ )			-0.6	$\text{mA}$
$V_{IK}$	Input Clamp Voltage ( $I_{in} = -18\text{ mA}$ )			-1.2	$\text{V}$
$V_{IH}$	Input HIGH Voltage	2.0			$\text{V}$
$V_{IL}$	Input LOW Voltage			0.8	$\text{V}$

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

**Table 5. 100LVELT PECL OUTPUT DC CHARACTERISTICS** ( $V_{CC} = 3.3\text{ V}$ ,  $GND = 0\text{ V}$  (Note 1))

Symbol	Characteristic	-40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
$I_{CC}$	Negative Power Supply Current	20	25	30	22	27	32	23	28	33	$\text{mA}$
$V_{OH}$	Output HIGH Voltage (Note 2)	2155	2280	2405	2155	2280	2405	2155	2280	2405	$\text{mV}$
$V_{OL}$	Output LOW Voltage (Note 2)	1355	1480	1605	1355	1480	1605	1355	1480	1605	$\text{mV}$

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

1. Output parameters vary 1:1 with  $V_{CC}$ .
2. All loading with  $50\ \Omega$  to  $V_{CC} - 2.0\text{ V}$ .

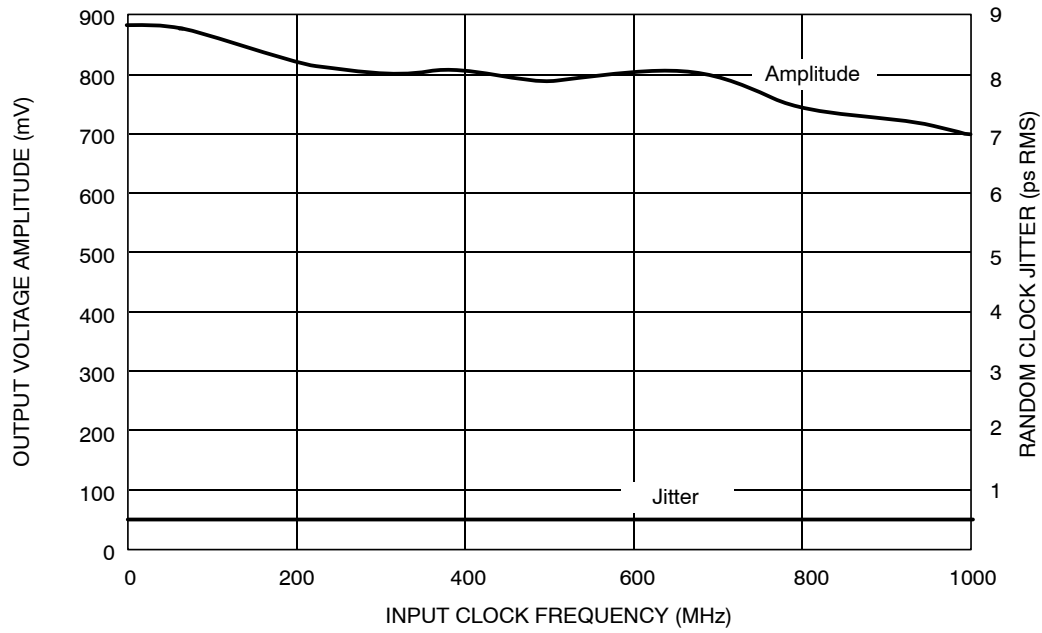
**Table 6. AC CHARACTERISTICS** ( $V_{CC} = 3.0\text{ V}$  to  $3.6\text{ V}$ ,  $GND = 0\text{ V}$  (Note 1))

Symbol	Characteristic	-40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
$f_{max}$	Maximum Input Clock Frequency (Figure 2)	600	800		600	800		600	800		$\text{MHz}$
$t_{PLH}$ , $t_{PHL}$	Propagation Delay to Output Differential	280	350	430	300	370	450	320	400	490	$\text{ps}$
$t_{SKEW}$	Device-to-Device Skew (Note 2)			250			250			250	$\text{ps}$
$t_{JITTER}$	Random Clock Jitter (RMS) (Figure 2)		< 1	< 2		< 1	< 2		< 1	< 2	$\text{ps}$
$t_r$ , $t_f$	Output Rise/Fall Times Q, $\bar{Q}$ (20% – 80%)	70	100	225	80	120	225	90	140	225	$\text{ps}$

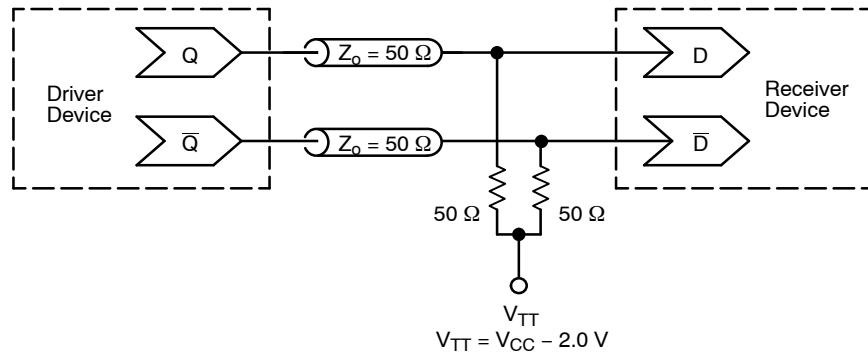
NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

1. Measured using a LVTTTL source, 50% duty cycle clock source. All loading with  $50\ \Omega$  to  $V_{CC} - 2.0\text{ V}$ .
2. Skew is measured between outputs under identical transitions.

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**Figure 2. Output Voltage Amplitude ( $V_{OUTpp}$ )/RMS Jitter vs. Input Clock Frequency at Ambient Temperature**

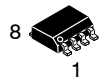


**Figure 3. Typical Termination for Output Driver and Device Evaluation**  
(See Application Note [AND8020/D](#) – Termination of ECL Logic Devices.)

## MC100LVELT20

### Resource Reference of Application Notes

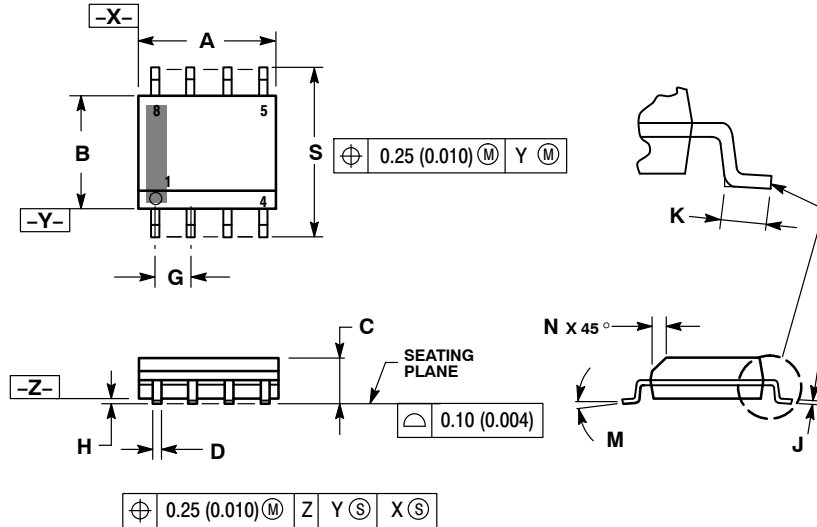
- AN1405/D** – ECL Clock Distribution Techniques
- AN1406/D** – Designing with PECL (ECL at +5.0 V)
- AN1503/D** – ECLinPS™ I/O SPICE Modeling Kit
- AN1504/D** – Metastability and the ECLinPS Family
- AN1568/D** – Interfacing Between LVDS and ECL
- AN1672/D** – The ECL Translator Guide
- AND8001/D** – Odd Number Counters Design
- AND8002/D** – Marking and Date Codes
- AND8020/D** – Termination of ECL Logic Devices
- AND8066/D** – Interfacing with ECLinPS
- AND8090/D** – AC Characteristics of ECL Devices



SCALE 1:1

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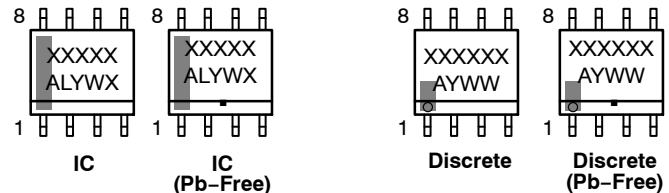
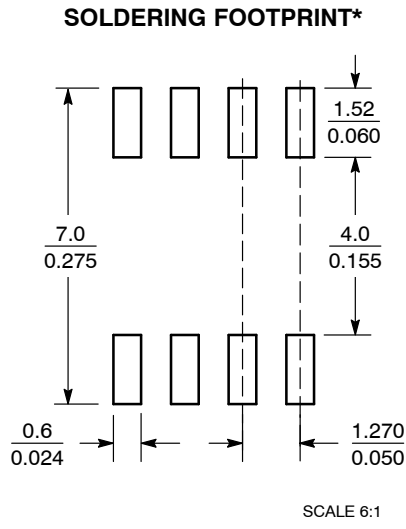


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0°	8°	0°	8°
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

GENERIC  
MARKING DIAGRAM\*



XXXXXX = Specific Device Code  
A = Assembly Location  
L = Wafer Lot  
Y = Year  
W = Work Week  
▪ = Pb-Free Package

XXXXXX = Specific Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
▪ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

\*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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**CASE 751-07**  
**ISSUE AK**

DATE 16 FEB 2011

<b>STYLE 1:</b> PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER	<b>STYLE 2:</b> PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. BASE, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1	<b>STYLE 3:</b> PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1	<b>STYLE 4:</b> PIN 1. ANODE 2. ANODE 3. ANODE 4. ANODE 5. ANODE 6. ANODE 7. ANODE 8. COMMON CATHODE
<b>STYLE 5:</b> PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE	<b>STYLE 6:</b> PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE	<b>STYLE 7:</b> PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd	<b>STYLE 8:</b> PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1
<b>STYLE 9:</b> PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON	<b>STYLE 10:</b> PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND	<b>STYLE 11:</b> PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1	<b>STYLE 12:</b> PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
<b>STYLE 13:</b> PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN	<b>STYLE 14:</b> PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	<b>STYLE 15:</b> PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON	<b>STYLE 16:</b> PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1
<b>STYLE 17:</b> PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC	<b>STYLE 18:</b> PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE	<b>STYLE 19:</b> PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1	<b>STYLE 20:</b> PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
<b>STYLE 21:</b> PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6	<b>STYLE 22:</b> PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND	<b>STYLE 23:</b> PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT	<b>STYLE 24:</b> PIN 1. BASE 2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE 6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE
<b>STYLE 25:</b> PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT	<b>STYLE 26:</b> PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC	<b>STYLE 27:</b> PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	<b>STYLE 28:</b> PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN
<b>STYLE 29:</b> PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1	<b>STYLE 30:</b> PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		

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